



P-Channel 40 V (D-S) 175 °C MOSFET

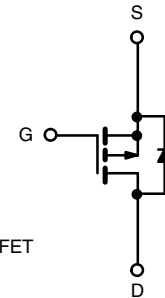
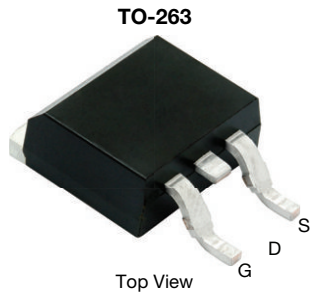
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d
-40	0.0042 at $V_{GS} = -10$ V	-110
	0.0062 at $V_{GS} = -4.5$ V	-110

FEATURES

- TrenchFET® Power MOSFET
- Low thermal resistance
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT



Ordering Information:

SUM110P04-04L-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C) ^d	$T_C = 25$ °C	I_D	-110	A
	$T_C = 125$ °C		-110	
Pulsed Drain Current		I_{DM}	-240	
Avalanche Current	L = 0.1 mH	I_{AS}	-75	
Single Pulse Avalanche Energy ^a		E_{AS}	281	mJ
Power Dissipation	$T_C = 25$ °C	P_D	375 ^c	W
	$T_A = 25$ °C ^b		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient PCB Mount ^b		R_{thJA}	40	°C/W
Junction-to-Case		R_{thJC}	0.4	

Notes

- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.
- Limited by package.



SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			-50	
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			-250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-120			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -30\text{ A}$		0.0034	0.0042	Ω
		$V_{GS} = -10\text{ V}, I_D = -30\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.0063	
		$V_{GS} = -10\text{ V}, I_D = -30\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.0076	
		$V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		0.005	0.0062	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -30\text{ A}$	20			S
Dynamic ^b						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		11 200		pF
Output Capacitance	C_{OSS}			1650		
Reverse Transfer Capacitance	C_{RSS}			1200		
Total Gate Charge ^c	Q_g	$V_{DS} = -20\text{ V}, V_{GS} = -10\text{ V}, I_D = -110\text{ A}$		235	350	nC
Gate-Source Charge ^c	Q_{gs}			45		
Gate-Drain Charge ^c	Q_{gd}			65		
Gate Resistance	R_g			3		Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -20\text{ V}, R_L = 0.18\text{ }\Omega$ $I_D \cong -110\text{ A}, V_{GEN} = -10\text{ V}, R_g = 2.5\text{ }\Omega$		25	40	ns
Rise Time ^c	t_r			30	45	
Turn-Off Delay Time ^c	$t_{d(off)}$			190	300	
Fall Time ^c	t_f			110	165	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$) ^b						
Continuous Current	I_S				-110	A
Pulsed Current	I_{SM}				-240	
Forward Voltage ^a	V_{SD}	$I_F = -85\text{ A}, V_{GS} = 0\text{ V}$		-1	-1.5	V
Reverse Recovery Time	t_{rr}	$I_F = -85\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		65	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			-3.7	-5.6	A
Reverse Recovery Charge	Q_{rr}			0.12	0.28	μC

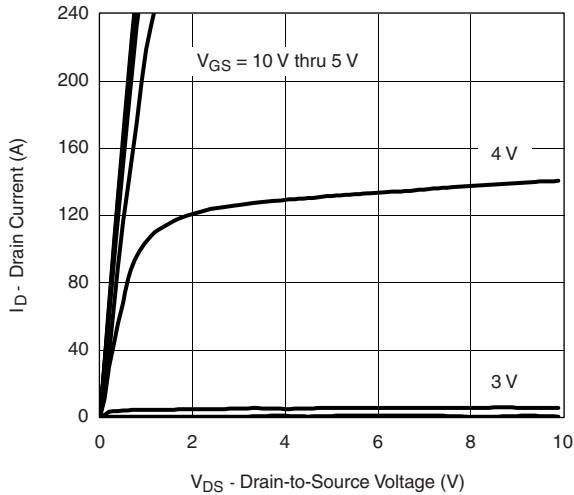
Notes

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

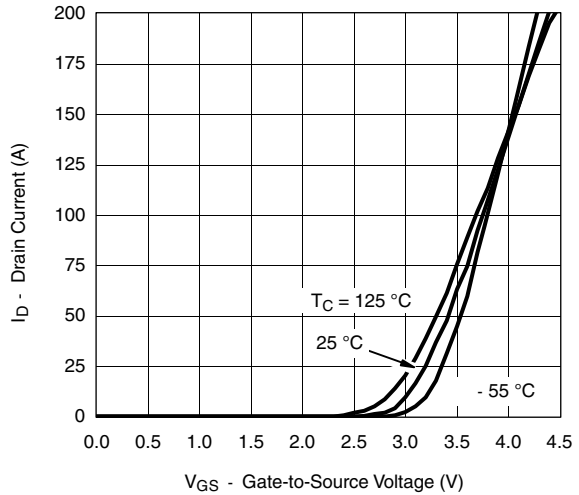
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



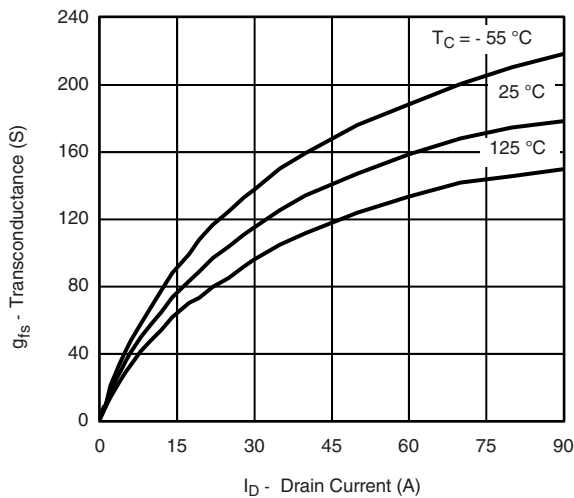
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



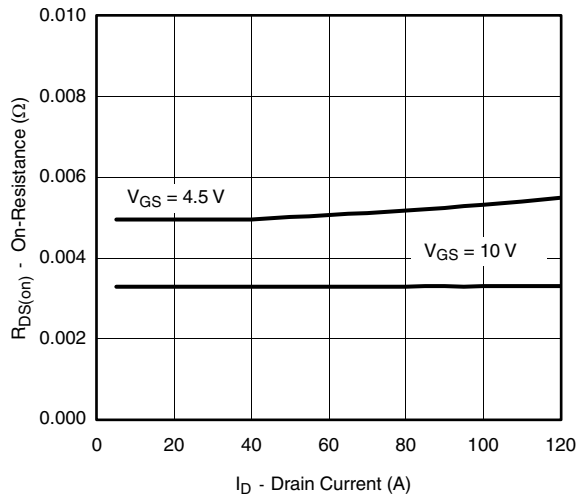
Output Characteristics



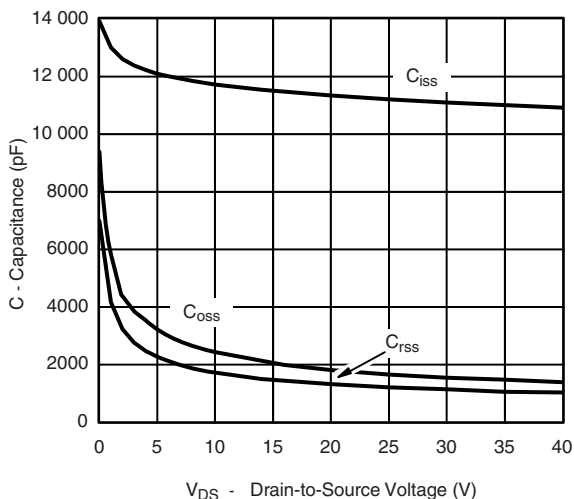
Transfer Characteristics



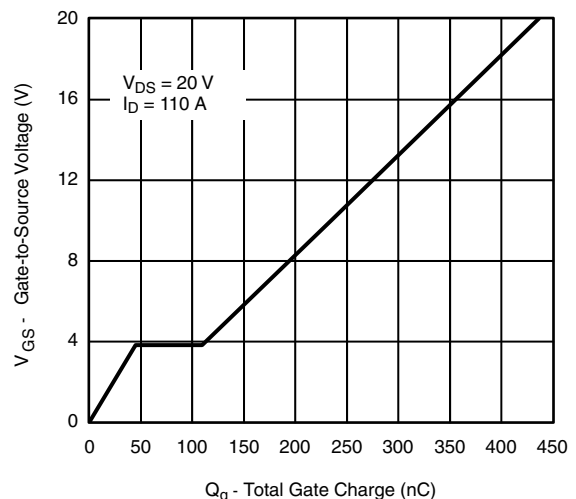
Transconductance



On-Resistance vs. Drain Current



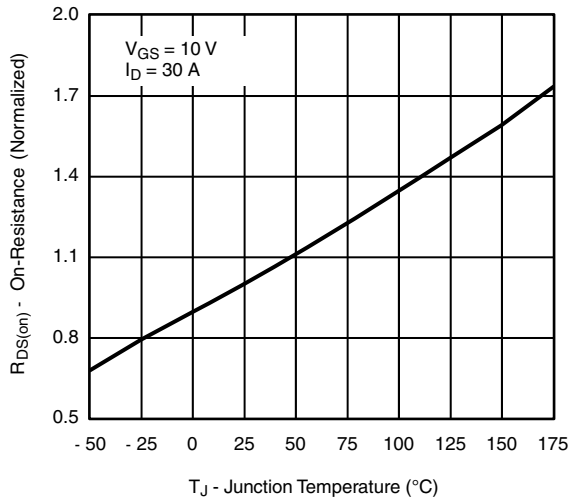
Capacitance



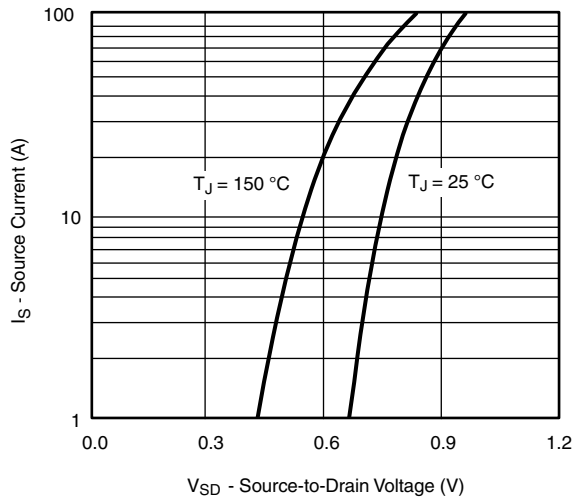
Gate Charge



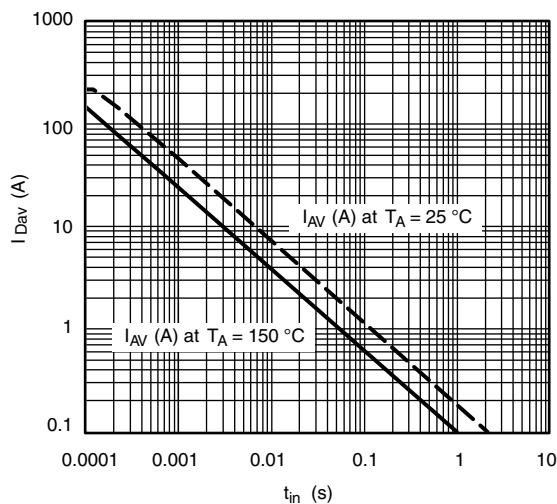
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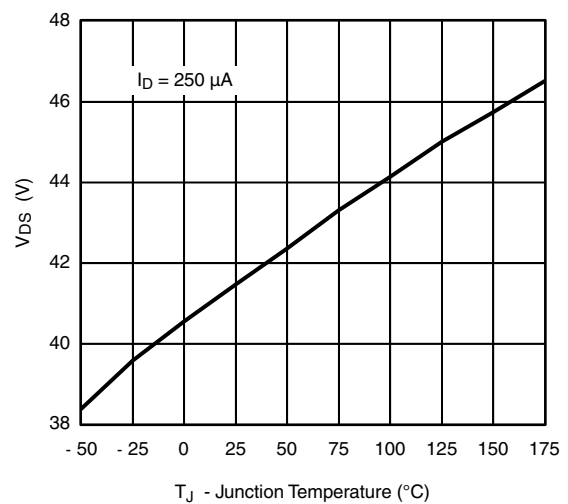
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



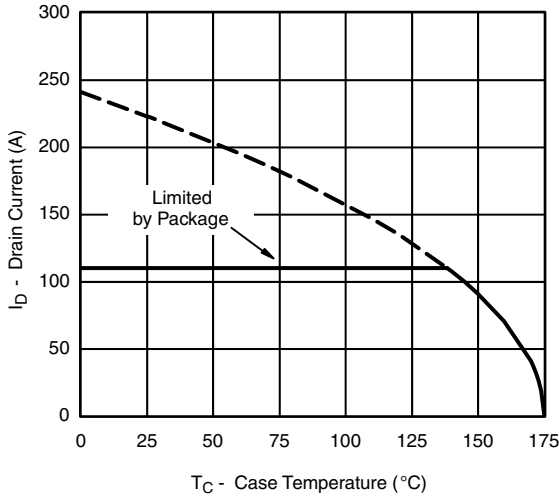
Avalanche Current vs. Time



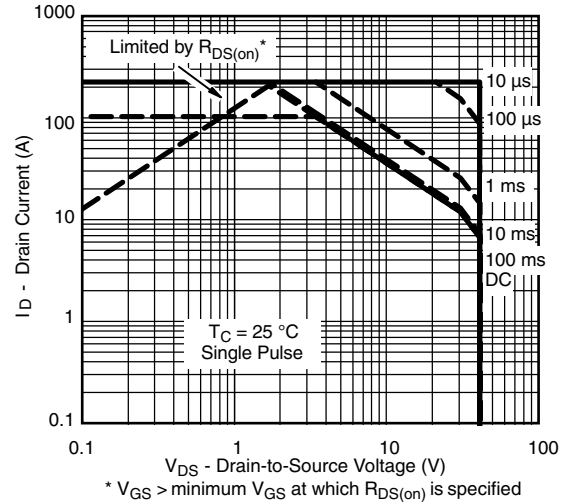
Drain Source Breakdown vs. Junction Temperature



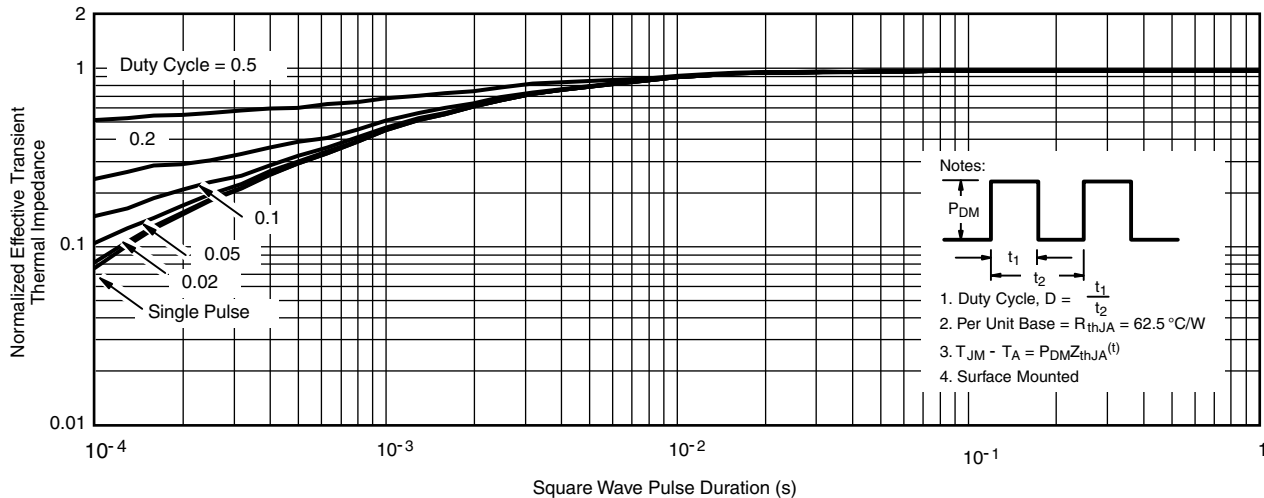
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



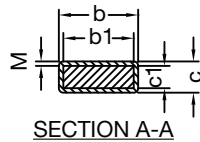
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-263 (D²PAK): 3-LEAD



DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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